S8	S7	S6	S5	S4	82	S1	Ref
327	49623	52626	18	&	165	75	Hits
S7 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)	S6 and @ad<"20040114"	(check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET MOSFET BJT transistor)	S2 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	S1 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	(324/602,600.ccls.) and @ad<"20040114"	(324/609.ccls.) and @ad<"20040114"	Search Query
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	DBs
O _R	O _R	O _R	OR.	O _R	OR.	OR.	Default Operator
O _N	ON	ON	O _N	ON ON	9 S	ON	Plurals
2005/05/12 15:53	2005/05/12 14:21	2005/05/12 13:00	2005/05/12 15:51	2005/05/13 13:26	2005/05/13 13:21	2005/05/16 06:57	Time Stamp

S15	S14	S13	S12	S11	S10	65
27	504	N	ω	11	18	206
\$14 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET MOSFET BJT transistor)	(455/127.1.ccls.) and @ad<"20040114"	S9 and battery near3 (charg\$3 near (level state status capacity))	S8 and battery near3 (charg\$3 near (level state status capacity))	S9 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1am) near3 (capacitor sampling)	S8 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1am) near3 (capacitor sampling)	S7 and ((capacitor sampling) near2 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
O _R	O _R	O _R	O _R	O _R	O _R	Q _R
Q.	S S	8	S _O	N N	O _N	ON
2005/05/12 13:00	2005/05/12 12:59	2005/05/12 14:18	2005/05/12 15:00	2005/05/12 14:39	2005/05/13 13:24	2005/05/12 14:22

S22	S21	S20	S19	S18	S17	S16
<u> </u>						
10883	11544	-	"	37	878	911
S21 and @ad<"20040114"	battery near3 (charg\$3 near (level state status capacity))	S19 and battery	S18 and (charg\$3 near2 (level state status capacity))	S17 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1amp (op adj amp)) near3 (capacitor sampling)	S16 and @ad<"20040114"	((capacitor sampling) near2 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
Q _R	O _R	O _R	Q	Q.	O _R	OR
O _N	Q	Q S	O _N	ON.	Q	ON
2005/05/12 14:38	2005/05/12 14:37	2005/05/12 14:25	2005/05/12 14:26	2005/05/12 15:08	2005/05/12 14:38	2005/05/12 14:21

2005/05/12 15:48	OFF	OR	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	14 (("5769873") or ("5627740") or ("5831562") or ("5963156") or ("6285220") or ("6426657") or ("6529049")).PN.		S29
2005/05/12 15:10	9	OR	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2 S27 and (amplifier op\$1amp (op adj amp)) near3 (capacitor sampling)		S28
2005/05/12 15:40	Q.	O _R	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	33 S26 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1amp (op adj amp))	ω	S27
2005/05/12 15:08	9	O _R	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	79 S24 and (capacitor sampling) same (sampl\$3 near2 voltage)	7	S26
2005/05/12 15:07	9	O _R	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	3 S24 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)		S25
2005/05/12 15:01	O _N	O _R	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	S7 and battery near3 (charg\$3 near (level state status capacity))	1025	S24
2005/05/12 15:02	N _O	Q.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	14 S22 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)	p.	S23

OR	TE LY A	\$34 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3	S36 4
OR	TA X TA A	S33 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1am) near3 US-PGPUB; (capacitor sampling) EPO; JPO; DERWENT; IBM_TDB	S35 126
PUB; OR PUB; O	L & L A B	S32 and (switch\$3 (charg\$3 adj transfer\$5)) near3 (amplifier op\$1am) near3 US-PGPUB; (capacitor sampling) EPO; JPO; DERWENT; IBM_TDB	S34 77
PUB; OR PUB; O	J & X A B	(327/91-96.ccls.) and @ad<"20040114" US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	S33 1599
PUB; OR PUB; OR DB	u ≷ĭăä	(327/9,55,56,337.ccls.) and @ad<"20040114" US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	S32 699
PUB; OR OR OR OB	u ≷ĭăã	S29 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) Same (sampl\$3 near2 voltage) DERWENT; DERWENT;	S31 1
SPUB; OR T; JPO; JENT; ICHT; ICHT; ICHT; ICHT	1 8 7 8 8	\$29 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 US-PGPUB; \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 USPAT; monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor) DERWENT; IBM_TDB	S30 3

	USPAT; EPO; JPO; DERWENT; TRM TDR	USPAT; EPO; JPO; DERWENT; IBM TDB
(341/122-125.ccls.) and @ad<"20040114"		US-PGPUB; USPAT; EPO; JPO;
(327/50-54.ccls.) and @ad<"20040114"	14" US-PGPUB; OR USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
easur\$5 comput\$3 calcul. 1\$3 recogniz\$3 inspect\$3 3 current near3 (resist\$5 l	S39 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 US-PGPUB; OR \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 USPAT; monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor) EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; transistor) EPO; JPO; DERWENT; IBM_TDB
asur\$5 comput\$3 calcul \$3 recogniz\$3 inspect\$3 current near3 (resist\$5 l	S38 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 US-PGPUB; OR \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 USPAT; monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor) EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; transistor) EPO; JPO; DERWENT; IBM_TDB
:r\$5)) same (amplifier o	S33 and (switch\$3 (charg\$3 adj transfer\$5)) same (amplifier op\$1am) same US-PGPUB; OR (capacitor sampling) EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
\$5)) same (amplifier o	S32 and (switch\$3 (charg\$3 adj transfer\$5)) same (amplifier op\$1am) same US-PGPUB; OR (capacitor sampling) EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
ur\$5 comput\$3 calcularecogniz\$3 inspect\$3 recogniz\$5 (resist\$5 f	S35 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 US-PGPUB; OR \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 USPAT; monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor) EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; transistor) EPO; JPO; DERWENT; IBM_TDB

S50	S49	S48	S47	S46	S45	1
				.		1,1 51
169	12	11	252	1380	738	
S45 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	S44 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	S43 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	S42 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 current near3 (resist\$5 FET transistor)	(323/282,353.ccls.) and @ad<"20040114"	(363/76,78,89.ccls.) and @ad<"20040114"	
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	USPAT; EPO; JPO; DERWENT; IBM_TDB
OR.	Q _R	O _R	OR.	Q _R	O _R	,
Q Q	Q.	Q.	Q _N	O _N	ON	. 1
2005/05/13 14:14	2005/05/13 14:47	2005/05/13 14:45	2005/05/13 14:13	2005/05/13 14:05	2005/05/13 14:03	

S57	S56	S55	S54	\$53	\$52	S51
1428	504	165	75	11	47	25
(324/111,522,713.ccls.) and @ad<"20040114"	(455/127.1.ccls.) and @ad<"20040114"	(324/602,600.ccls.) and @ad<"20040114"	(324/609.ccls.) and @ad<"20040114"	(check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current) near3 (resist\$5 FET transistor)	S50 and (switch\$3 (charg\$3 adj transfer\$5)) same (amplifier op\$1am) same (capacitor sampling)	S47 and (switch\$3 (charg\$3 adj transfer\$5)) same (amplifier op\$1am) same (capacitor sampling)
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB				
S _R	Q _R	O _R	Q _R	O _R	O _R	Q _R
ON	ON	Q	ON	Q	Q	Q
2005/05/13 15:16	2005/05/13 15:16	2005/05/13 15:16	2005/05/13 15:15	2005/05/13 14:52	2005/05/13 14:16	2005/05/13 14:16

(0	ιn	(1)	()	S	S	S
S64	S63	S62	S61	S60	S59	S58
,_	0	0	0	ω	H	11
\$32 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)	\$45 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)	\$44 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)	\$43 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)	\$42 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)	S58 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)	S53 and @ad<"20040114"
US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB				
O _R	O _R	O _R	Q _R	O _R	O _R	Q _R
Q	Q	Q	Q	Q.	Q	O Z
2005/05/13 15:49	2005/05/13 15:38	2005/05/13 15:37	2005/05/13 15:37	2005/05/13 15:45	2005/05/13 15:52	2005/05/13 15:51

(check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) near2 current)
\$57 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)
\$56 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)
\$55 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)
\$54 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)
\$33 and (check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 ((two both) adj (way direction))) adj current)

EPO; JPO; DERWENT; IBM_TDB	EPO; DERW IBM_1				
Q _R	UB;	US-PGPUB; USPAT;	33 S75 and (capacitor sampling)	578 133	
OR	SPUB; T; JPO; /ENT; TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	6 S76 and (sampl\$3 near2 voltage)	S77	
O _R	SPUB; T; JPO; /ENT; TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	78 S75 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor))	S76 7	
Q.	SPUB; T; JPO; /ENT;	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	18 S74 and @ad<"20040114"	S75 318	
O _R	SPUB; JPO; JENT; TDB	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	(check\$3 detect\$3 sens\$3 measur\$5 comput\$3 calculat\$3 \$2valuat\$3 examin\$5 test\$3 determin\$3 recogniz\$3 inspect\$3 anal\$5 monitor\$3 diagnos\$3 identif\$7) near3 ((bi\$1direction\$3 two\$1way two\$1direction both\$way both\$1direction ((two both) adj (way direction))) near2 current)	S74 344	
OR	JPO; JPO; JBOT;	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	6 S71 and (capacitor sampling) same (sampl\$3 near2 voltage)	S73	
Q _R	PUB; T; JPO; ENT;	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	1 S71 and ((capacitor sampling) near4 (resist\$5 FET MOSFET BJT transistor)) same (sampl\$3 near2 voltage)	S72	

S79 13 S78 and (sampl\$3 near2 voltage) US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB ON 2005/05/16 07:27					
S78 and (sampl\$3 near2 voltage) US-PGPUB; OR ON USPAT; EPO; JPO; DERWENT; IBM_TDB					579
S78 and (sampl\$3 near2 voltage) US-PGPUB; OR ON USPAT; EPO; JPO; DERWENT; IBM_TDB					
voltage) US-PGPUB; OR ON USPAT; EPO; JPO; DERWENT; IBM_TDB					13
QR QN					S78 and (sampl\$3 near2 voltage)
O _Z	IBM_TD8	DERWENT;	EPO; JPO;	USPAT;	US-PGPUB;
-					유
2005/05/16 07:27					
				<u>-</u>	9